

Amendments to the Claims

1. *(Currently Amended)* An electric device comprising:
 - a substrate ~~(2,42,50)~~ having a main surface of a first material, and
 - a nanostructure ~~(1,44,51)~~ of a second material,wherein the first and second materials having a mutual lattice mismatch, and wherein the nanostructure being supported by and being in epitaxial relationship with the substrate.
2. *(Currently Amended)* A device according to claim 1, wherein the nanostructure ~~(1,44,51)~~ is in electrical contact with the substrate ~~(2,42,50)~~.
3. *(Currently Amended)* A device according to claim 2, wherein the resistance between the nanostructure ~~(1,44,51)~~ and the substrate ~~(2,42,50)~~ is below 10^{-5} Ohm cm^2 .
4. *(Currently Amended)* A device according to claim 1, wherein the nanostructure ~~(1,44,51)~~ is a nanotube and/or the nanostructure is a nanowire.
5. *(Currently Amended)* A device according to claim 1, wherein a lattice mismatch between the substrate ~~(2,42,50)~~ and the nanostructure(s) ~~(1,44,51)~~ is smaller than 10%.
6. *(Currently Amended)* A device according to claim 1, wherein the nanostructure ~~(1,44,51)~~ is a substantially single-crystal nanostructure.
7. *(Original)* A device according to claim 1, wherein a plurality of nanostructures are arranged in an array.
8. *(Original)* A device according to claim 1, wherein the electric device is a gate-around transistor.

9. *(Currently Amended)* A device according to claim 8, further comprising a first dielectric ~~(45,53)~~ and wherein the first dielectric is in contact with at least a section of the nanostructure(s) ~~(1,44,51)~~.

10. *(Currently Amended)* A device according to claim 9, further comprising a first conductive material ~~(46,55,65)~~ and wherein the first conductive material is electrically insulated from the substrate by the first dielectric ~~(45,53)~~.

11. *(Currently Amended)* A device according to claim 10, further comprising a second dielectric ~~(54)~~ and wherein the second dielectric is electrically insulating the first conductive material ~~(46,55,65)~~ from the nanostructure ~~(1,44,51)~~.

12. *(Original)* A device according to claim 11 wherein the first dielectric is thicker than the second dielectric.

13. *(Currently Amended)* A device according to claim 1, further comprising a second conductive material ~~(48,59)~~ and wherein the second conductive material is in contact with at least one nanostructure ~~(1,44,51)~~.

14. *(Currently Amended)* A device according to claim 13, further comprising at least a third dielectric ~~(47,56,57)~~, the at least third dielectric insulating the second conductive material ~~(48,59)~~ from the first conductive material ~~(46,55,65)~~.

15. *(Currently Amended)* A method of growing a second material in epitaxial relationship with a first material, the second material and the first material having a mutual lattice mismatch, the method comprising the steps of:

- providing a substrate ~~(2,42,50)~~ of the first material,
- forming a nanostructure ~~(1,44,51)~~ of the second material by a growth method,

wherein the first material comprising at least one element from a first group in the periodic table and the second material comprising at least one element from a second group, the second group being different from the first group, and wherein the nanostructure being supported by and in epitaxial relationship with the substrate.

16. *(Currently Amended)* A method according to claim 15, wherein the nanostructure is grown according to the vapour-liquid-solid (~~VLS~~) growth method. |